

$V_{DRM}$	=	5200 V
$I_{T(AV)M}$	=	2830 A
$I_{T(RMS)}$	=	4450 A
$I_{TSM}$	=	$50.5 \cdot 10^3$ A
$V_{T0}$	=	0.990 V
$r_T$	=	0.237 m $\Omega$

# Phase Control Thyristor

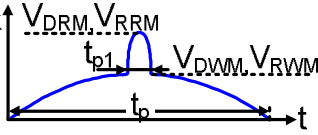
## 5STP 25L5200

Doc. No. 5SYA1008-08 May. 20

- Patented free-floating silicon technology
- Low on-state and switching losses
- Designed for traction, energy and industrial applications
- Optimum power handling capability
- Interdigitated amplifying gate

### Blocking

Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	5STP 25L5200	Unit
Max. surge peak forward and reverse blocking voltage	$V_{DSM}$ , $V_{RSM}$	$t_p = 10$ ms, $f = 5$ Hz $T_{vj} = 5 \dots 125$ °C, Note 1	5200	V
Max repetitive peak forward and reverse blocking voltage	$V_{DRM}$ , $V_{RRM}$	$f = 50$ Hz, $t_p = 10$ ms, $t_{p1} = 250$ $\mu$ s, $T_{vj} = 5 \dots 125$ °C, Note 1, Note 2	5200	V
Max crest working forward and reverse voltages	$V_{DWM}$ , $V_{RWM}$		3470	V
Critical rate of rise of commutating voltage	$dv/dt_{crit}$	Exp. to $0.67 \cdot V_{DRM}$ , $T_{vj} = 125$ °C	2000	V/ $\mu$ s

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward leakage current	$I_{DRM}$	$V_{DRM}$ , $T_{vj} = 125$ °C			400	mA
Reverse leakage current	$I_{RRM}$	$V_{RRM}$ , $T_{vj} = 125$ °C			400	mA

Note 1: Voltage de-rating factor of 0.11% per °C is applicable for  $T_{vj}$  below +5 °C.

Note 2: Recommended minimum ratio of  $V_{DRM} / V_{DWM}$  or  $V_{RRM} / V_{RWM} = 2$ . See App. Note 5SYA 2051.

### Mechanical data

Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Mounting force	$F_M$		63	70	84	kN
Acceleration	a	Device unclamped			50	m/s <sup>2</sup>
Acceleration	a	Device clamped			100	m/s <sup>2</sup>

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Weight	m				1.45	kg
Housing thickness	H	$F_M = 70$ kN, $T_a = 25$ °C	26.37		27.02	mm
Surface creepage distance	$D_s$		36			mm
Air strike distance	$D_a$		15			mm

1) Maximum rated values indicate limits beyond which damage to the device may occur

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## On-state

### Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Average on-state current	$I_{T(AV)M}$	Half sine wave, $T_c = 70\text{ °C}$			2830	A
RMS on-state current	$I_{T(RMS)}$				4450	A
Peak non-repetitive surge current	$I_{TSM}$	$t_p = 10\text{ ms}$ , $T_{vj} = 125\text{ °C}$ , sine half wave, $V_D = V_R = 0\text{ V}$ , after surge			$50.5 \cdot 10^3$	A
Limiting load integral	$I^2t$				$12.8 \cdot 10^6$	A <sup>2</sup> s
Peak non-repetitive surge current	$I_{TSM}$	$t_p = 10\text{ ms}$ , $T_{vj} = 125\text{ °C}$ , sine half wave, $V_R = 0.6 \cdot V_{RRM}$ , after surge			$37.0 \cdot 10^3$	A
Limiting load integral	$I^2t$				$6.85 \cdot 10^6$	A <sup>2</sup> s

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
On-state voltage	$V_T$	$I_T = 3000\text{ A}$ , $T_{vj} = 125\text{ °C}$		1.60	1.70	V
Threshold voltage	$V_{(T0)}$	$I_T = 1300\text{ A} - 4000\text{ A}$ , $T_{vj} = 125\text{ °C}$			0.990	V
Slope resistance	$r_T$				0.237	mΩ
Holding current	$I_H$	$T_{vj} = 25\text{ °C}$			125	mA
		$T_{vj} = 125\text{ °C}$			60	mA
Latching current	$I_L$	$T_{vj} = 25\text{ °C}$			500	mA
		$T_{vj} = 125\text{ °C}$			250	mA

## Switching

### Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Critical rate of rise of on-state current	$di/dt_{crit}$	$T_{vj} = 125\text{ °C}$ , $I_T = 3000\text{ A}$ , $V_D \leq 0.67 \cdot V_{DRM}$ , $I_{GM} = 2\text{ A}$ , $t_r = 0.5\text{ }\mu\text{s}$			250	A/ $\mu\text{s}$
		Cont. $f = 50\text{ Hz}$			1000	A/ $\mu\text{s}$
Circuit-commutated turn-off time	$t_q$	$T_{vj} = 125\text{ °C}$ , $I_T = 2000\text{ A}$ , $V_R = 200\text{ V}$ , $di_T/dt = -1.5\text{ A}/\mu\text{s}$ , $V_D \leq 0.67 \cdot V_{DRM}$ , $dV_D/dt = 20\text{ V}/\mu\text{s}$			500	$\mu\text{s}$

### Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Reverse recovery charge	$Q_{rr}$	$T_{vj} = 125\text{ °C}$ , $I_T = 2000\text{ A}$ , $V_R = 200\text{ V}$ , $di_T/dt = -1.5\text{ A}/\mu\text{s}$	3200	3960	4400	$\mu\text{As}$
Reverse recovery current	$I_{RM}$		50	71	90	A
Gate turn-on delay time	$t_{gd}$	$T_{vj} = 25\text{ °C}$ , $V_D = 0.4 \cdot V_{RM}$ , $I_{GM} = 2\text{ A}$ , $t_r = 0.5\text{ }\mu\text{s}$			3	$\mu\text{s}$

## Triggering

Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Peak forward gate voltage	$V_{FGM}$				12	V
Peak forward gate current	$I_{FGM}$				10	A
Peak reverse gate voltage	$V_{RGM}$				10	V
Average gate power loss	$P_{G(AV)}$		see Fig. 7			W

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Gate-trigger voltage	$V_{GT}$	$T_{vj} = 25\text{ °C}$			2.6	V
Gate-trigger current	$I_{GT}$	$T_{vj} = 25\text{ °C}$			400	mA
Gate non-trigger voltage	$V_{GD}$	$V_D = 0.4 \cdot V_{DRM}, T_{vjmax} = 125\text{ °C}$			0.3	V
Gate non-trigger current	$I_{GD}$	$V_D = 0.4 \cdot V_{DRM}, T_{vjmax} = 125\text{ °C}$			10	mA

## Thermal

Maximum rated values <sup>1)</sup>

Parameter	Symbol	Conditions	min	typ	max	Unit
Operating junction temperature range	$T_{vj}$				125	°C
Storage temperature range	$T_{stg}$		-40		140	°C

Characteristic values

Parameter	Symbol	Conditions	min	typ	max	Unit
Thermal resistance junction to case	$R_{th(j-c)}$	Double-side cooled $F_m = 63... 84\text{ kN}$			7	K/kW
	$R_{th(j-c)A}$	Anode-side cooled $F_m = 63... 84\text{ kN}$			14	K/kW
	$R_{th(j-c)C}$	Cathode-side cooled $F_m = 63... 84\text{ kN}$			14	K/kW
Thermal resistance case to heatsink	$R_{th(c-h)}$	Double-side cooled $F_m = 63... 84\text{ kN}$			1.5	K/kW
	$R_{th(c-h)}$	Single-side cooled $F_m = 63... 84\text{ kN}$			3	K/kW

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

i	1	2	3	4
$R_i$ (K/kW)	4.851	1.425	0.697	0.026
$\tau_i$ (s)	0.5262	0.0587	0.0056	0.0007

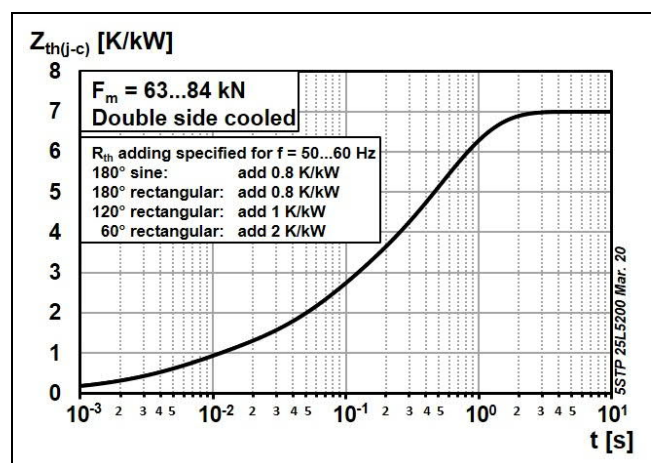


Fig. 1 Transient thermal impedance (junction-to-case) vs. time

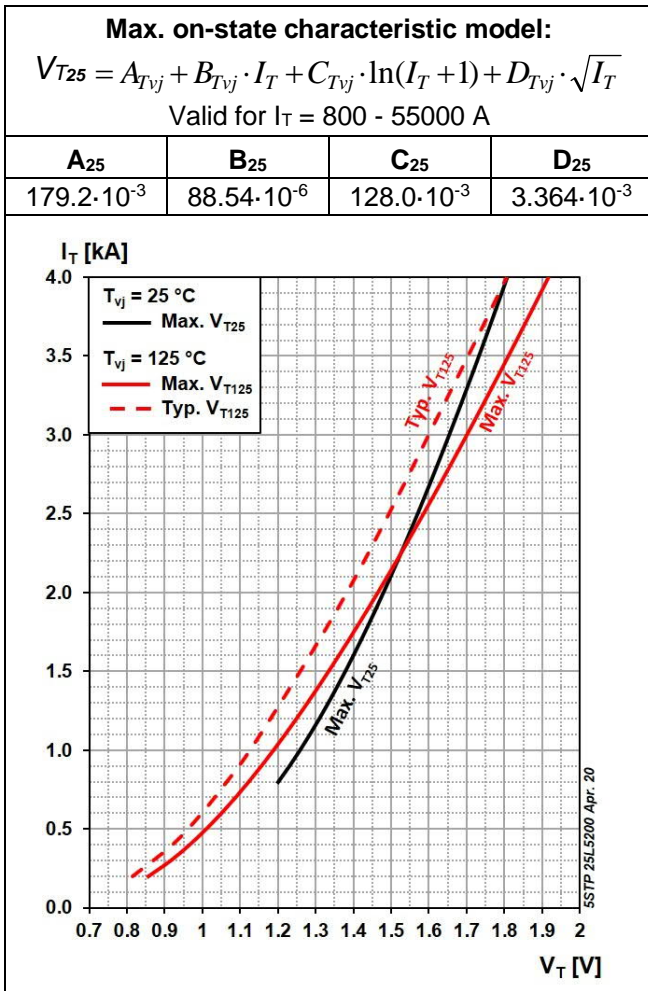


Fig. 2 On-state voltage characteristics

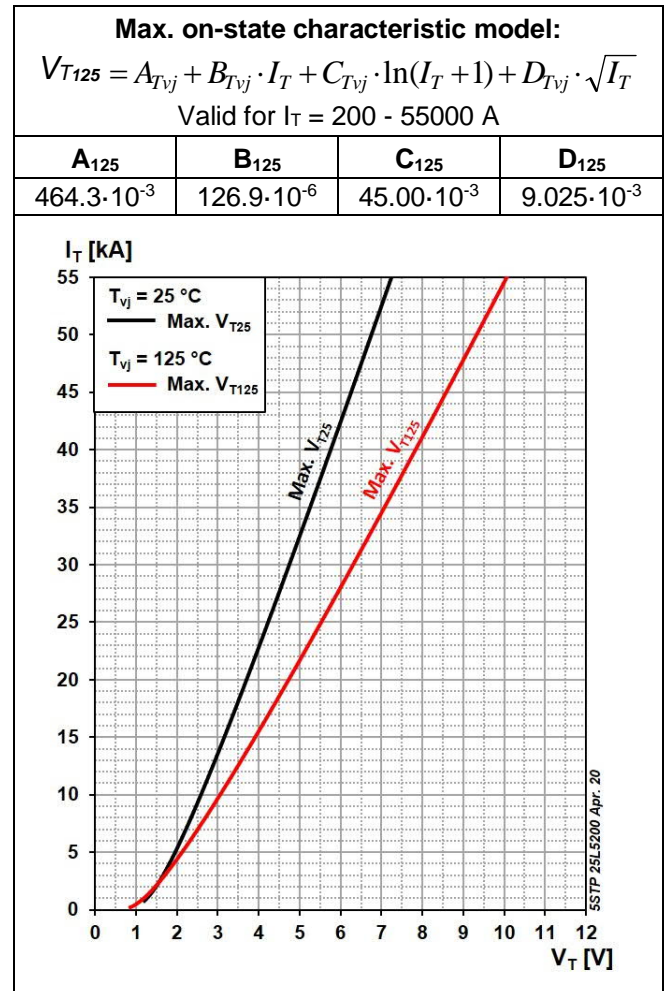


Fig. 3 On-state voltage characteristics

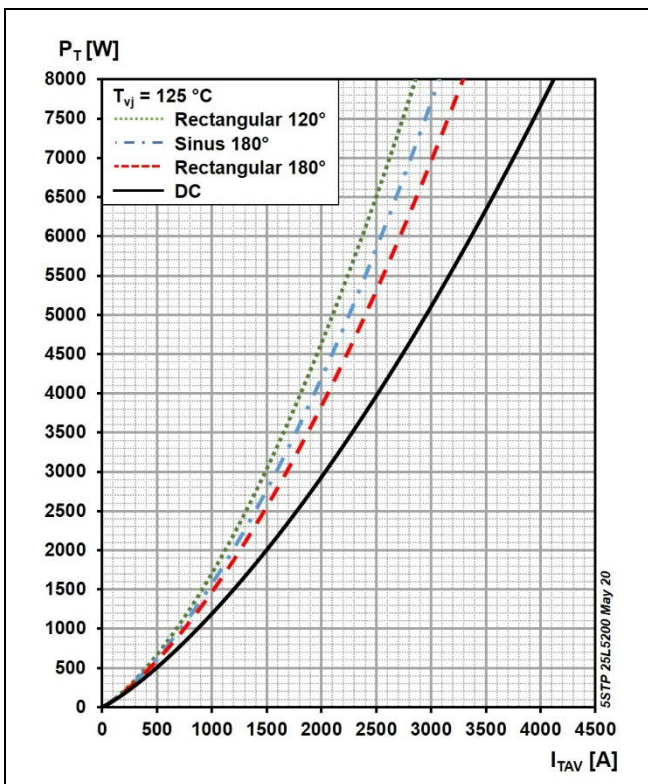


Fig. 4 On-state power dissipation vs. mean on-state current, turn-on losses excluded

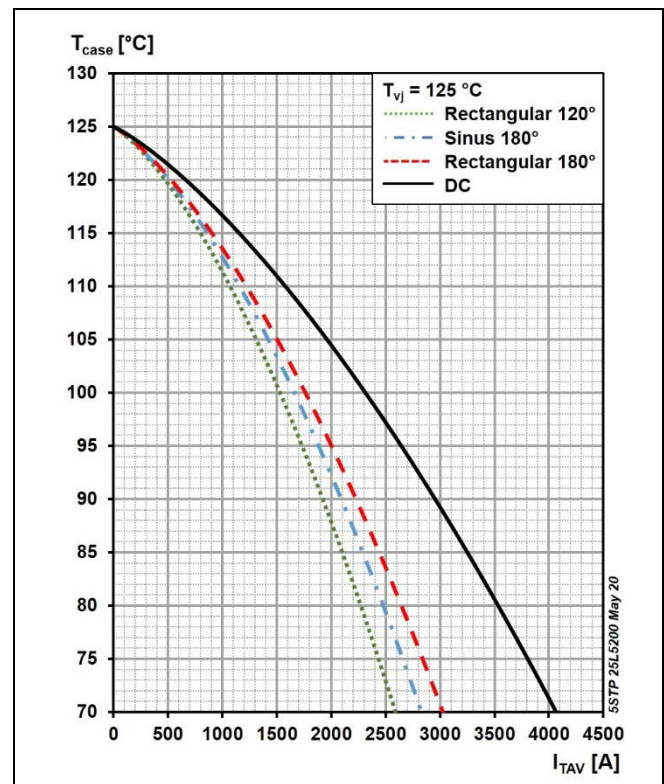


Fig. 5 Max. permissible case temperature vs. mean on-state current, switching losses ignored



Fig. 6 Recommended gate current waveform

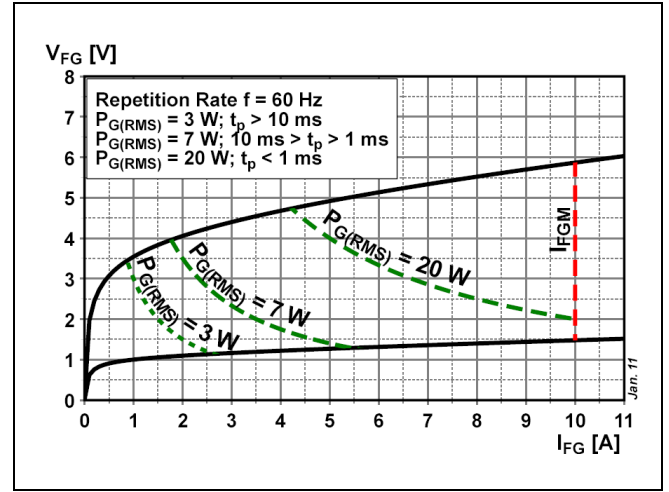


Fig. 7 Max. peak gate power loss

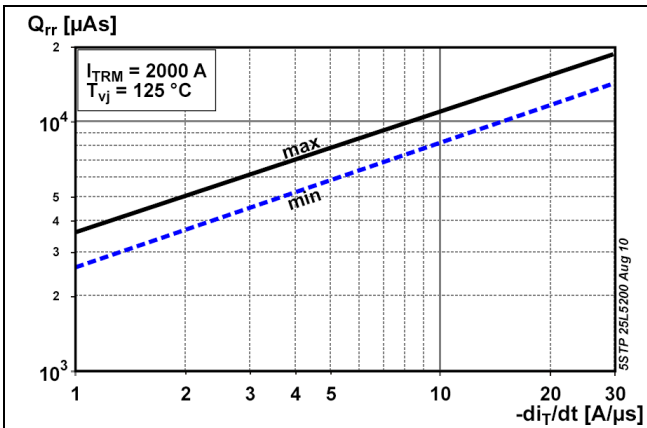


Fig. 8 Reverse recovery charge vs. decay rate of on-state current

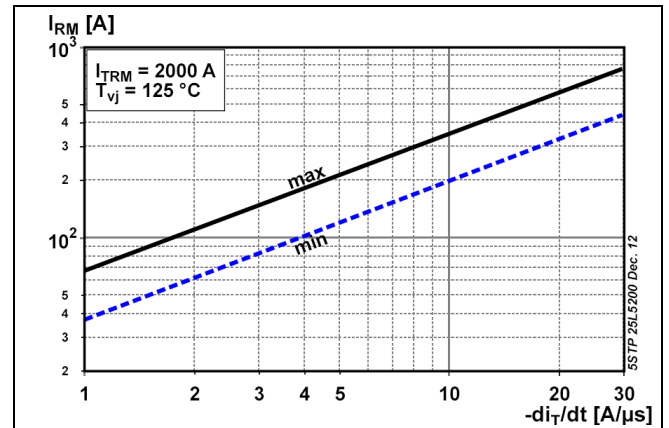


Fig. 9 Peak reverse recovery current vs. decay rate of on-state current



# Turn-on and Turn-off losses

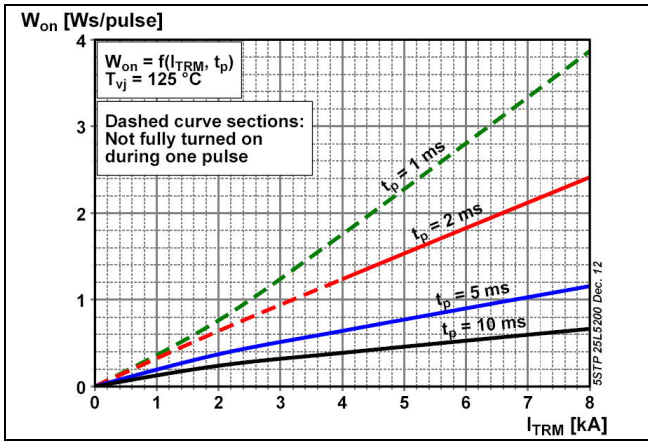


Fig. 10 Turn-on energy, half sinusoidal waves

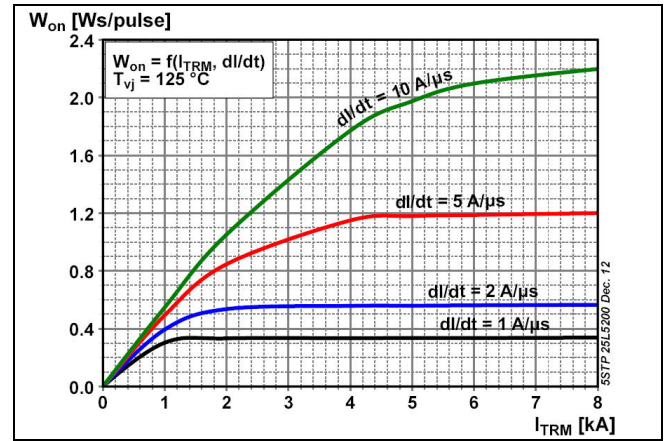


Fig. 11 Turn-on energy, rectangular waves

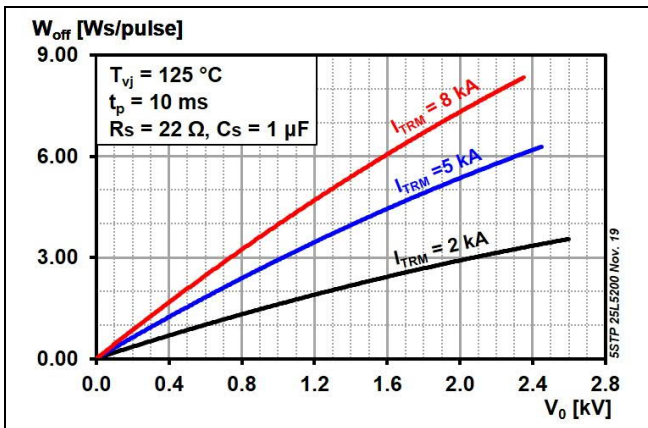


Fig. 12 Typical turn-off energy, half sinusoidal waves

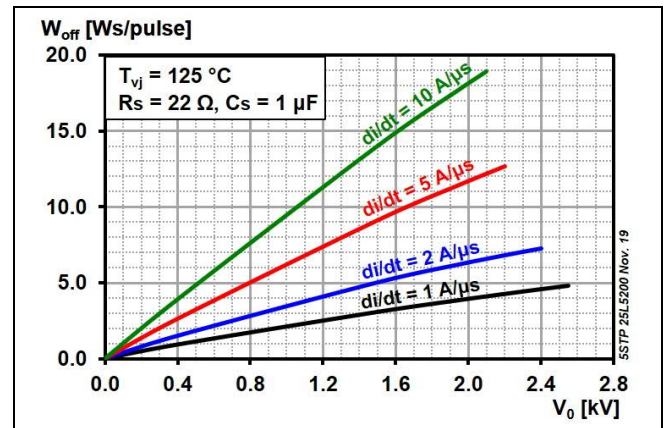


Fig. 13 Typical turn-off energy, rectangular waves

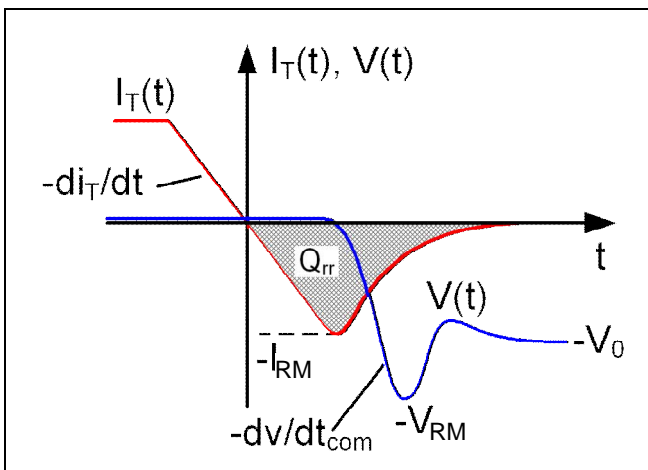


Fig. 14 Current and voltage waveforms at turn-off

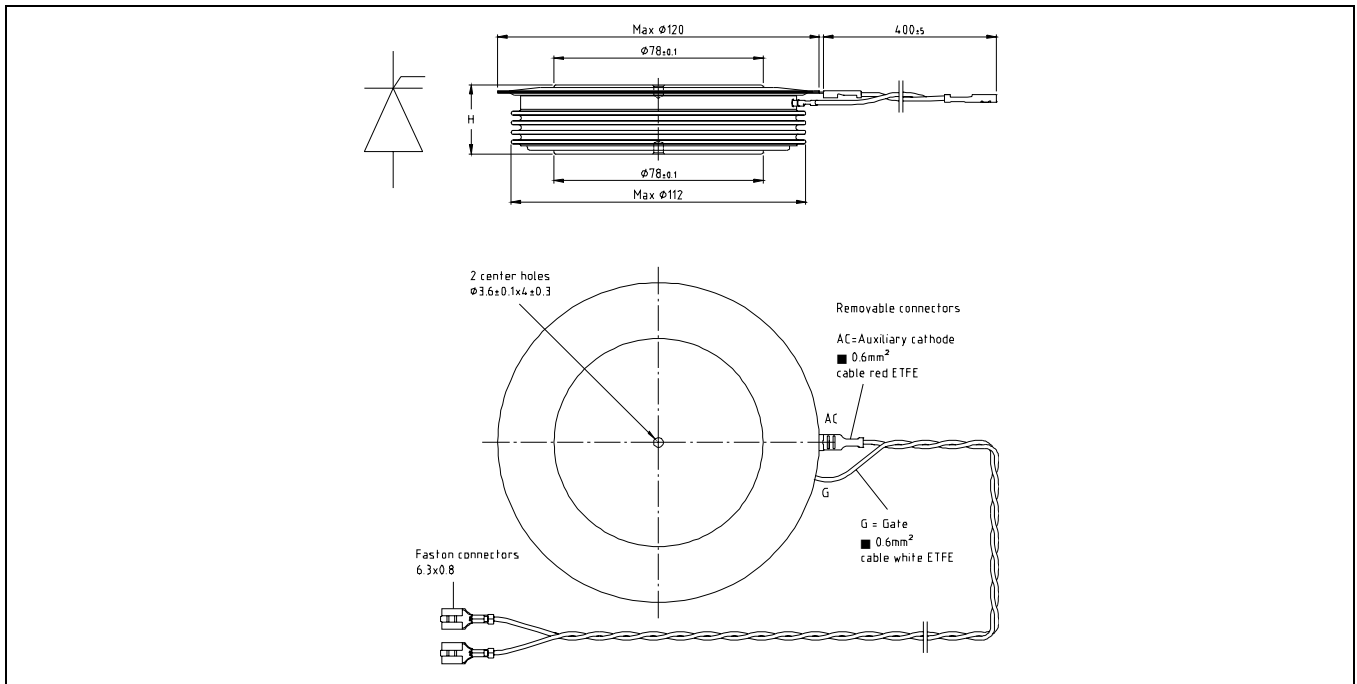
**Total power loss for repetitive waveforms:**

$$P_{TOT} = P_T + W_{on} \cdot f + W_{off} \cdot f$$

where

$$P_T = \frac{1}{T} \int_0^T I_T \cdot V_T(I_T) dt$$

Fig. 15 Relationships for power loss



**Fig. 16** Device Outline Drawing

### Related documents:

5SYA 2020	Design of RC-Snubbers for Phase Control Applications
5SYA 2049	Voltage definitions for phase control and bi-directionally controlled thyristors
5SYA 2051	Voltage ratings of high power semiconductors
5SYA 2034	Gate-drive recommendations for phase control and bi-directionally controlled thyristors
5SYA 2036	Recommendations regarding mechanical clamping of Press-Pack High Power Semiconductors
5SYA 2102	Surge currents for Phase Control Thyristors
5SZK 9118	General Environmental Conditions for High Power Semiconductors

Please refer to <http://www.abb.com/semiconductors> for current version of documents.

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